

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re U.S. Patent Application of )  
HASEGAWA )  
Application Number: To Be Assigned )  
Filed: Concurrently Herewith )  
For: ACTIVE MATRIX DISPLAY DEVICE )

Honorable Assistant Commissioner  
for Patents  
Washington, D.C. 20231

**PRELIMINARY AMENDMENT**

Sir:

Applicant has amended the claims in order to remove the multiple dependencies contained therein in accordance with standard U.S. practice, thereby reducing the basic filing fee.

No new matter has been added to the application as a result of this amendment. Prior to an examination on the merits, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please substitute claim 6 currently on file with the following amended claim:

6. (Amended) The active matrix display device according to claim 1, wherein the gate signal line is made of aluminum.

Please substitute claim 7 currently on file with the following amended claim:

7. (Amended) The active matrix display device according to claim 1, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.

Please substitute claim 8 currently on file with the following amended claim:

8. (Amended) The active matrix display device according to claim 1, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.

Please substitute claim 10 currently on file with the following amended claim:

10. (Amended) The active matrix display device according to claim 1, wherein the active matrix device is liquid crystal device.

Please add the following new claims:

11. (Added) The active matrix display device according to claim 2, wherein the gate signal line is made of aluminum.
12. (Added) The active matrix display device according to claim 3, wherein the gate signal line is made of aluminum.
13. (Added) The active matrix display device according to claim 4, wherein the gate signal line is made of aluminum.
14. (Added) The active matrix display device according to claim 2, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.
15. (Added) The active matrix display device according to claim 3, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.

16. (Added) The active matrix display device according to claim 4, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.
17. (Added) The active matrix display device according to claim 2, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.
18. (Added) The active matrix display device according to claim 3, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.
19. (Added) The active matrix display device according to claim 4, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.
20. (Added) The active matrix display device according to claim 17, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.
21. (Added) The active matrix display device according to claim 18, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.

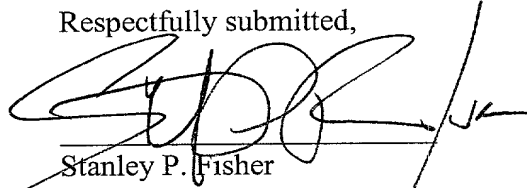
22. (Added) The active matrix display device according to claim 19, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.
23. (Added) The active matrix display device according to claim 2, wherein the active matrix device is liquid crystal device.
24. (Added) The active matrix display device according to claim 3, wherein the active matrix device is liquid crystal device.
25. (Added) The active matrix display device according to claim 4, wherein the active matrix device is liquid crystal device.
26. (Added) The active matrix display device according to claim 5, wherein the active matrix device is liquid crystal device.

**REMARKS**

Applicant has amended claim 6 and added claims 11, 12 and 13, amended claim 7 and added claims 14, 15 and 16, amended claim 8 and added claims 17, 18 and 19, added claims 20, 21 and 22, amended claim 10 and added claims 23, 24, 25 and 26. Applicant has amended the claims in order to remove the multiple dependencies contained therein in accordance with standard U.S. practice, thereby reducing the basic filing fee. No new matter has been added to the application as a result of this amendment.

In view of the above amendments and Applicant's comments stated herein, Applicant respectfully requests an early and favorable action on the merits.

Respectfully submitted,



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**August 2, 2001**

MARKED-UP CLAIMS

a gate electrode of each of the second thin-film transistors is made of a material different than a wiring layer or electrode and electrically connected to the wiring layer or electrode;

the gate electrode of the first thin-film transistor is made of the same material as that of each of the second thin-film transistors; and

the gate signal line is made of the same material as the wiring layer or electrode.

6. The active matrix display device according to ~~any one~~ of claims 1 ~~to 4~~, wherein the gate signal line is made of aluminum.

7. The active matrix display device according to ~~any one~~ of claims 1 ~~to 4~~, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.

8. The active matrix display device according to ~~any one~~ of claims 1 ~~to 4~~, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.

9. The active matrix display device according to claim 8, wherein the metal layers are formed at the same time as a